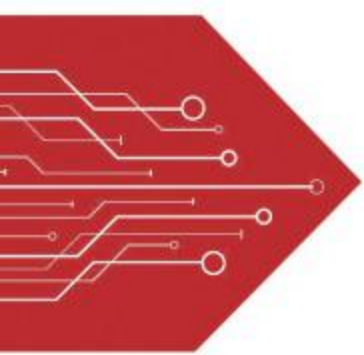


MSKSEMI

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT

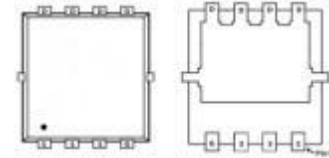


PLED

Product data sheet

General Description

These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

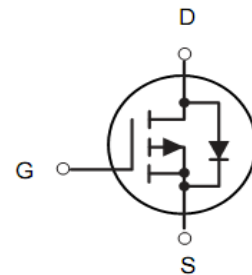


DFN5X6-8L

BVDSS	RDSON	ID
-18V	2.3mΩ	-80A

Features

- -18V,-80A, $R_{DS(ON)} = 2.7m\Omega @ V_{GS} = -10V$
- Improved dv/dt capability
- Fast switching
- Green Device Available



P-Channel MOSFET

Applications

- Notebook
- Load Switch
- Networking
- Hand-Held Instruments

Absolute Maximum Ratings $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-18	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Drain Current – Continuous ($T_c=25^\circ C$)	-80	A
	Drain Current – Continuous ($T_c=100^\circ C$)	-54	A
I_{DM}	Drain Current – Pulsed ¹	-360	A
P_D	Power Dissipation ($T_c=25^\circ C$)	41.67	W
	Power Dissipation – Derate above $25^\circ C$	0.33	W/ $^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	3	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-18	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =-1mA	---	-0.008	---	V/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-20V , V _{GS} =0V , T _J =25°C	---	---	-1	uA
		V _{DS} =-16V , V _{GS} =0V , T _J =125°C	---	---	-30	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±12V , V _{DS} =0V	---	---	±500	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V , I _D =-20A	---	2.3	3.0	mΩ
		V _{GS} =-2.5V , I _D =-20A	---	3.3	4.5	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-0.4	-0.6	-1.0	V
ΔV _{GS}	V _{GS(th)} Temperature Coefficient		---	-3.44	---	mV/°C
g _{fs}	Forward Transconductance	V _{DS} =-10V , I _S =-3A	---	30	---	S

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{2, 3}	V _{DS} =-16V , V _{GS} =-4.5V , I _D =-5A	---	149	225	nC
Q _{gs}	Gate-Source Charge ^{2, 3}		---	14.4	22	
Q _{gd}	Gate-Drain Charge ^{2, 3}		---	42.8	65	
T _{d(on)}	Turn-On Delay Time ^{2, 3}	V _{DD} =-15V , V _{GS} =-4.5V , R _G =25Ω I _D =-1A	---	21.2	42	nS
T _r	Rise Time ^{2, 3}		---	20.6	40	
T _{d(off)}	Turn-Off Delay Time ^{2, 3}		---	26	52	
T _f	Fall Time ^{2, 3}		---	400	600	
C _{iss}	Input Capacitance	V _{DS} =-15V , V _{GS} =0V , F=1MHz	---	12000	16000	pF
C _{oss}	Output Capacitance		---	1670	2500	
C _{rss}	Reverse Transfer Capacitance		---	730	1100	
R _g	Gate resistance	V _{GS} =0V , V _{DS} =0V , F=1MHz	---	2.6	---	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V , Force Current	---	---	-85	A
I _{SM}	Pulsed Source Current		---	---	-190	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V , I _S =-1A , T _J =25°C	---	---	-1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
3. Essentially independent of operating temperature.

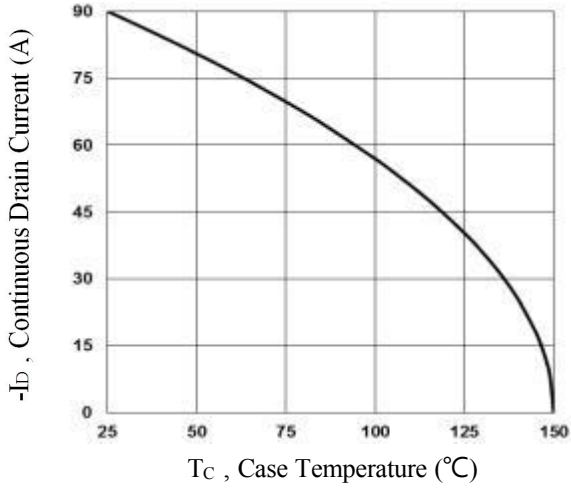


Fig.1 Continuous Drain Current vs. T_c

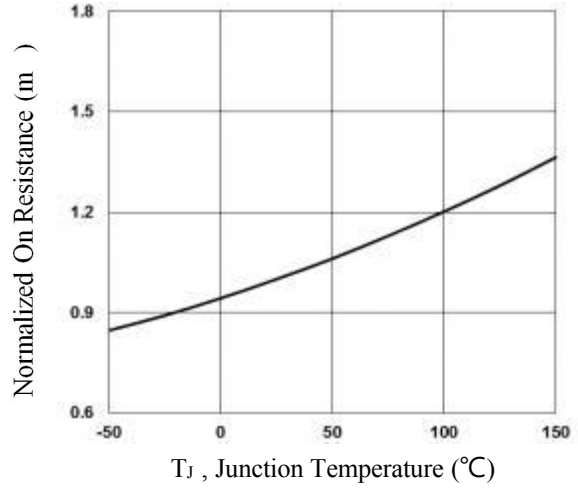


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

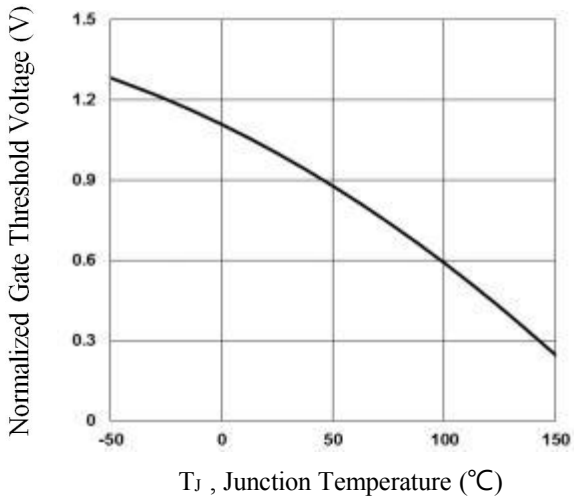


Fig.3 Normalized V_{th} vs. T_j

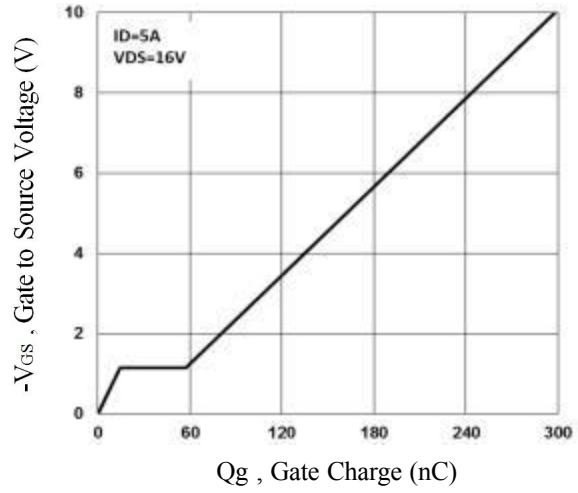


Fig.4 Gate Charge Waveform

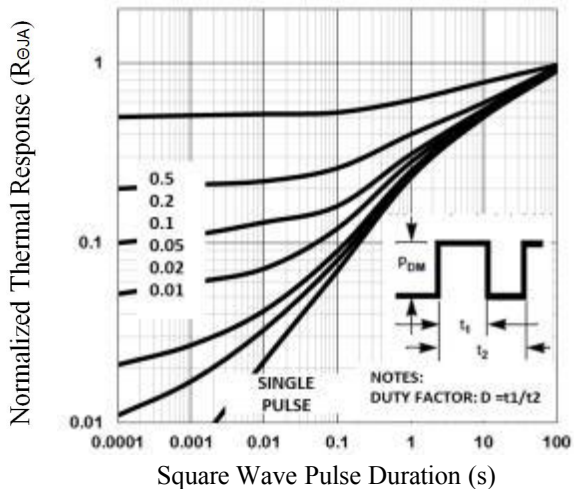


Fig.5 Normalized Transient Response

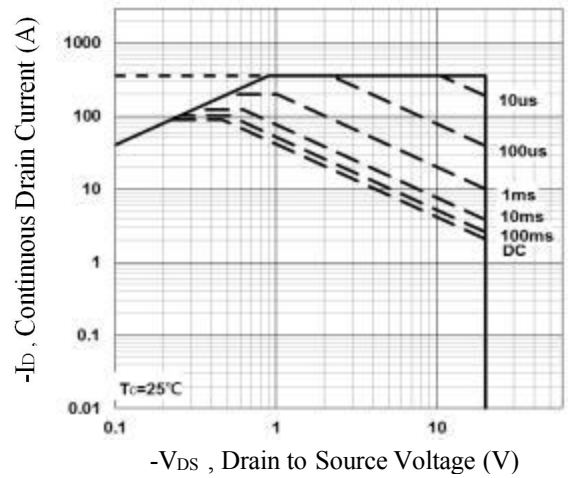


Fig.6 Maximum Safe Operation Area

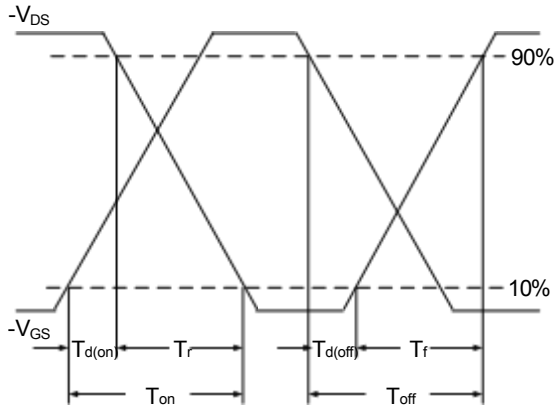


Fig.7 Switching Time Waveform

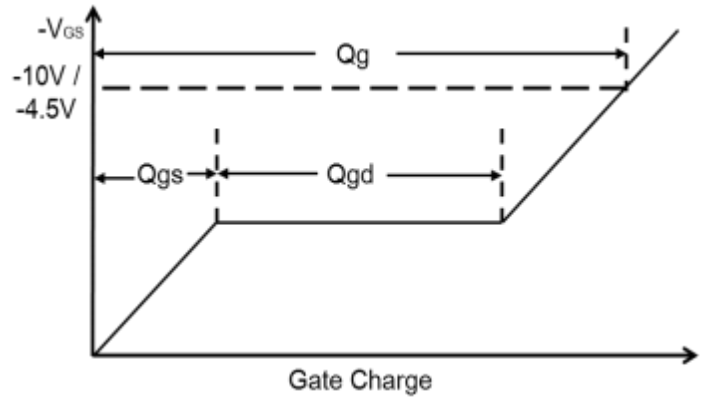
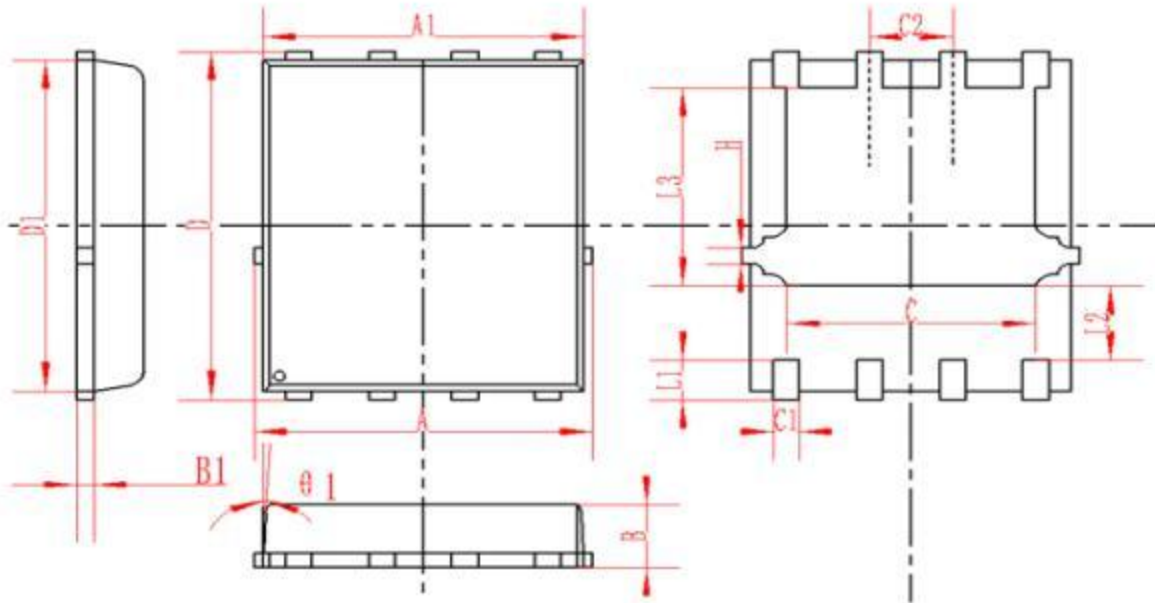


Fig.8 Gate Charge Waveform

DFN5X6-8L Package Information



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
B	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010

REEL SPECIFICATION

P/N	PKG	QTY
MSK20P80GNF	DFN5X6-8L	5000

Attention

- Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.
- MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MSKSEMI Semiconductor products described or contained herein.
- Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- MSKSEMI Semiconductor strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.
- Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringement of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the MSKSEMI Semiconductor product that you intend to use.